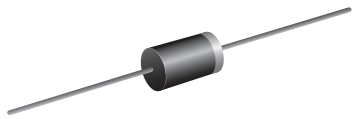
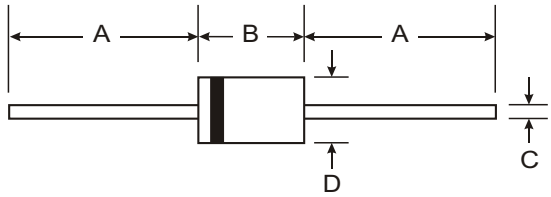
11DQ03 - 11DQ10

SCHOTTKY BARRIER RECTIFIER DIODES

VOLTAGE RANGE: 30 - 100V
CURRENT: 1.1 A





Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability

Mechanical Data

- Case: DO-41, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

DO-41		
Dim	**Min**	**Max**
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	11DQ 03	11DQ 04	11DQ 05	11DQ 06	11DQ 09	11DQ 10	Unit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	30	40	50	60	90	100	V
Maximum RMS Voltage	V_{RMS}	21	28	35	42	63	70	V
Maximum DC Blocking Voltage	V_{DC}	30	40	50	60	90	100	V
Maximum Average Forward Current	$I_{F(AV)}$	1.1						A
at Ambient Temperature	Ta	58		40		25		°C
Maximum Peak Forward Surge Current single half sine wave superimposed on rated load	I_{FSM}	42		26		42		A
Maximum Forward Voltage at I_F = 1.1 A	V_F	0.52		0.56		0.74		V
Maximum Reverse Current at Rated DC Blocking Voltage T_J = 125 °C	I_R	6		11		6		mA
Junction Temperature Range	T_J	- 40 to + 125						°C
Storage Temperature Range	T_{STG}	- 65 to + 150						°C

RATING AND CHARACTERISTIC CURVES (11DQ03 - 11DQ10)

FIG.1 - FORWARD CURRENT DERATING CURVE

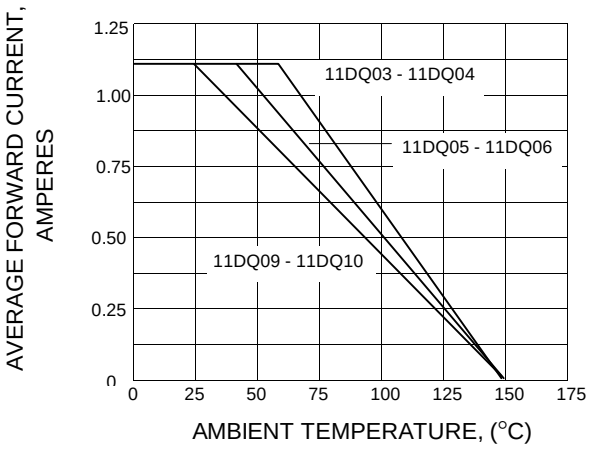


FIG.2 - MAXIMUM FORWARD SURGE CURRENT

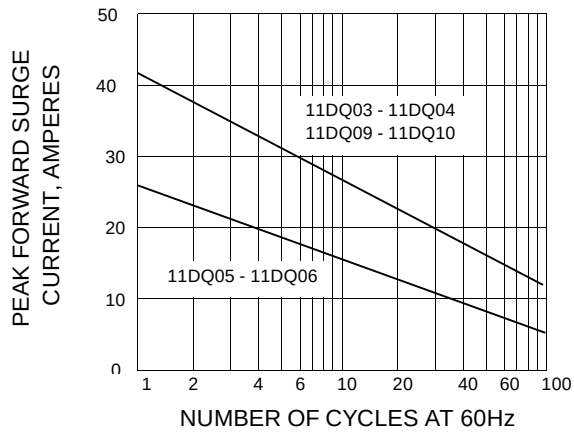


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

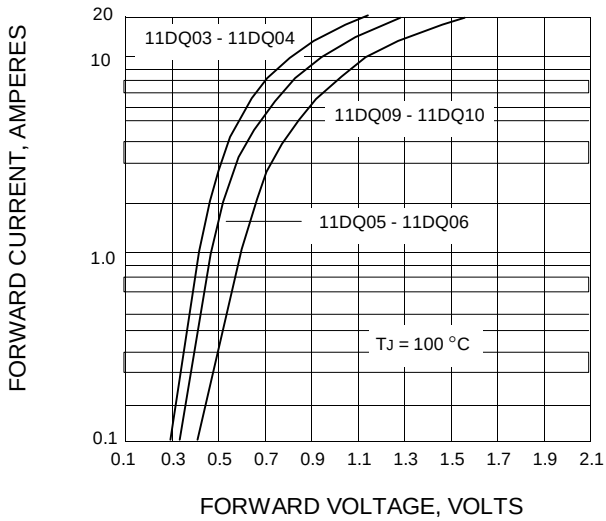


FIG.4 - TYPICAL REVERSE CHARACTERISTICS